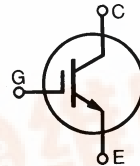




Ultra-Low $V_{CE(sat)}$ IGBT

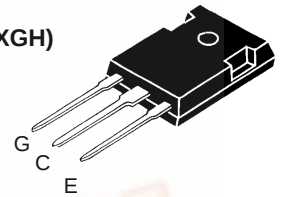
IXGH 60N60
IXGK 60N60
IXGT 60N60

$V_{CES} = 600\text{ V}$
 $I_{C25} = 75\text{ A}$
 $V_{CE(sat)} = 1.7\text{ V}$

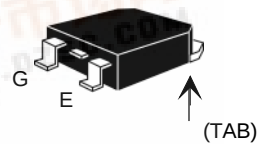


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$, limited by leads	75	A
I_{C90}	$T_C = 90^\circ\text{C}$	60	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	200	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10\text{ }\Omega$ Clamped inductive load, $L = 30\text{ }\mu\text{H}$	$I_{CM} = 100$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Weight	TO-247	6	g
	TO-264	10	g
	TO-268	4	g

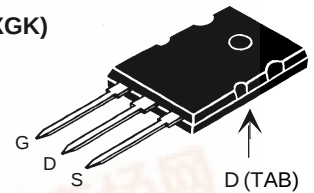
TO-247 AD (IXGH)



TO-268 (IXGT)



TO-264 (IXGK)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247 AD, TO-264, TO-268
- New generation HDMOS™ process
- Low $V_{CE(sat)}$ for minimum on-state conduction losses
- High current handling capability
- MOS Gate turn-on drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

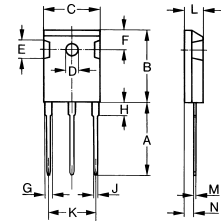
Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Low losses, high efficiency
- High power density
- High power, surface mount package

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250\text{ }\mu\text{A}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250\text{ }\mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0\text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			200 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			1.7 V

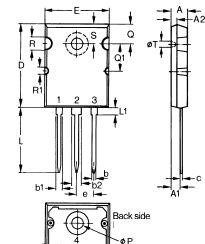
Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	30	55	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		3700	pF
C_{oes}			290	pF
C_{res}			86	pF
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		130	nC
Q_{ge}			30	nC
Q_{gc}			45	nC
t_{d(on)}	Inductive load, T_j = 25°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH, V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _j or increased R _G		50	ns
t_{ri}			25	ns
t_{d(off)}			300	600 ns
t_{fi}			360	570 ns
E_{off}			8	15 mJ
t_{d(on)}	Inductive load, T_j = 125°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _j or increased R _G		50	ns
t_{ri}			25	ns
E_{on}			3	mJ
t_{d(off)}			650	ns
t_{fi}			550	ns
E_{off}			17	mJ
R_{thJC}				0.42 K/W
R_{thCK}	(IXGH)		0.25	K/W
	(IXGK)		0.15	K/W

TO-247 AD (IXFH) Outline



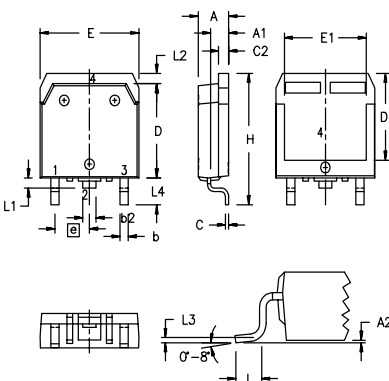
Dim.	Millimeter Min. Max.	Inches Min. Max.
A	19.81 20.32	0.780 0.800
B	20.80 21.46	0.819 0.845
C	15.75 16.26	0.610 0.640
D	3.55 3.65	0.140 0.144
E	4.32 5.49	0.170 0.216
F	5.4 6.2	0.212 0.244
G	1.65 2.13	0.065 0.084
H	- 4.5	- 0.177
J	1.0 1.4	0.040 0.055
K	10.8 11.0	0.426 0.433
L	4.7 5.3	0.185 0.209
M	0.4 0.8	0.016 0.031
N	1.5 2.49	0.087 0.102

TO-264 AA (IXFK) Outline



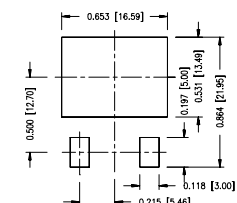
Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.82 5.13	.190 .202
A1	2.54 2.89	.100 .114
A2	2.00 2.10	.079 .083
b	1.12 1.42	.044 .056
b1	2.39 2.69	.094 .106
b2	2.90 3.09	.114 .122
c	0.53 0.83	.021 .033
D	25.91 26.16	1.020 1.030
E	19.81 19.96	.780 .786
e	5.46 BSC	.215 BSC
J	0.00 0.25	.000 .010
K	0.00 0.25	.000 .010
L	20.32 20.83	.800 .820
L1	2.29 2.59	.090 .102
P	3.17 3.66	.125 .144
Q	6.07 6.27	.239 .247
Q1	8.38 8.69	.330 .342
R	3.81 4.32	.150 .170
R1	1.78 2.29	.070 .090
S	6.04 6.30	.238 .248
T	1.57 1.83	.062 .072

TO-268AA (IXFT) (D³ PAK)



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.9 5.1	.193 .201
A1	2.7 2.9	.106 .114
A2	.02 .25	.001 .010
b	1.15 1.45	.045 .057
b2	1.9 2.1	.075 .083
C	.4 .65	.016 .026
D	13.80 14.00	.543 .551
E	15.85 16.05	.624 .632
E1	13.3 13.6	.524 .535
e	5.45 BSC	.215 BSC
H	18.70 19.10	.736 .752
L	2.40 2.70	.094 .106
L1	1.20 1.40	.047 .055
L2	1.00 1.15	.039 .045
L3	0.25 BSC	.010 BSC
L4	3.80 4.10	.150 .161

Min. Recommended Footprint



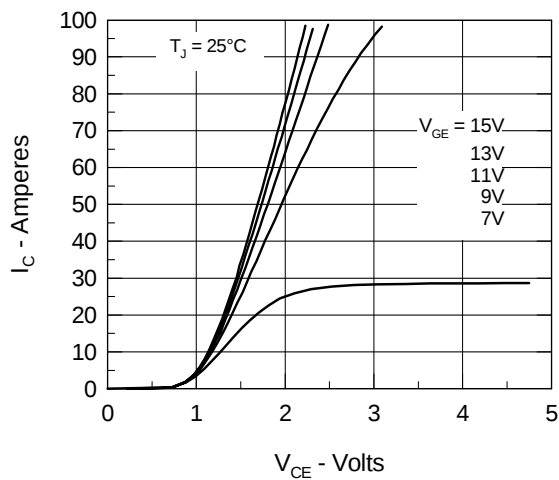


Fig. 1. Saturation Voltage Characteristics

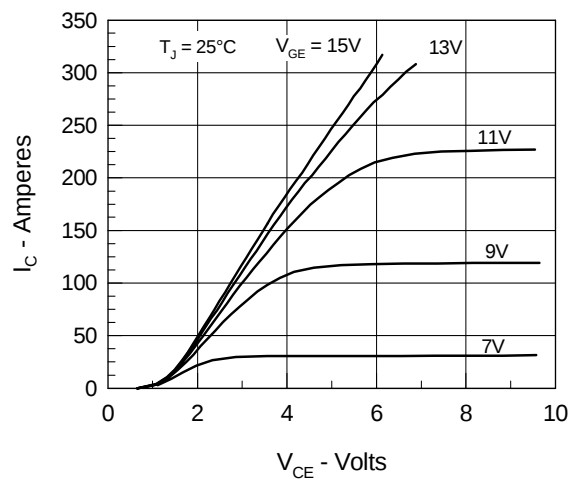


Fig. 2. Extended Output Characteristics

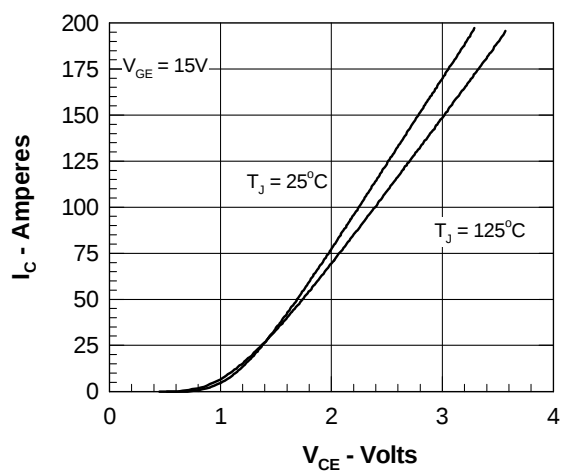


Fig. 3. Saturation Voltage Characteristics

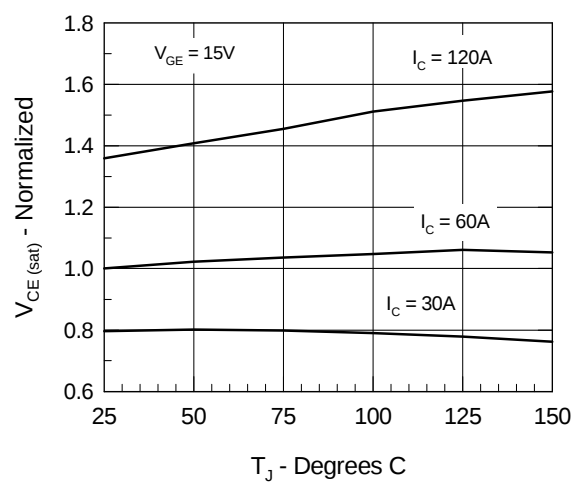


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

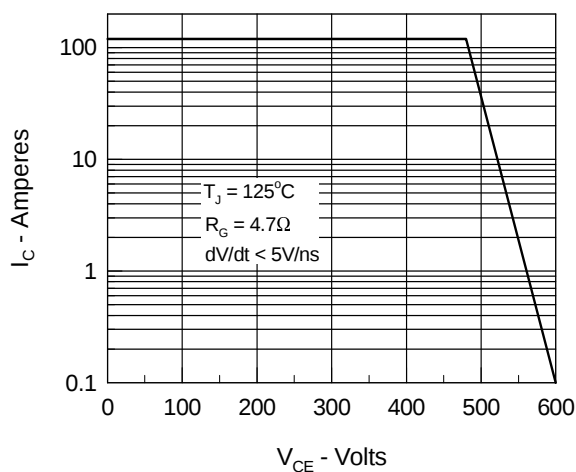


Fig. 5. Turn-off Safe Operating Area

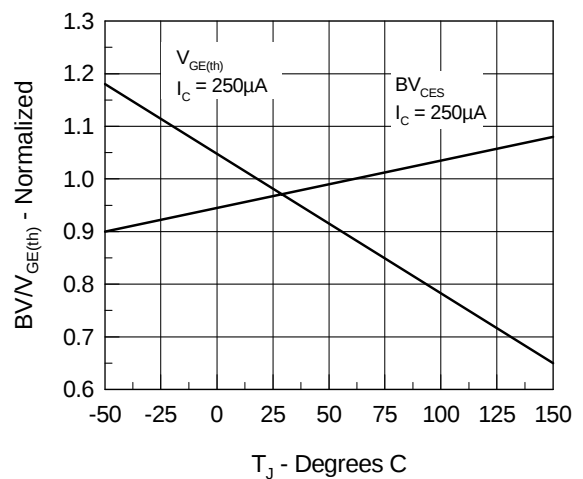


Fig. 6. Temperature Dependence of BV_{CES} & $V_{GE(th)}$

